# NPN Epitaxial Silicon Transistor

### KSC1845

#### **Features**

- Audio Frequency Low-Noise Amplifier
- Complement to KSA992
- This is a Pb-Free Device

#### **MAXIMUM RATINGS** (Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	120	V
V <sub>CEO</sub>	Collector-Emitter Voltage	120	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	50	mA
Ι <sub>Β</sub>	Base Current	10	mA
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

# **THERMAL CHARACTERISTICS** (Values are at $T_A = 25^{\circ}C$ unless otherwise noted.) (Note 1)

Symbol	Parameter	Value	Unit
$P_{D}$	Power Dissipation	500	mW
	Derate Above 25°C	4	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	250	°C/W

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.



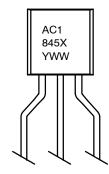
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TO-92 3 4.83x4.76 LEADFORMED CASE 135AR

#### **MARKING DIAGRAM**



A = Assembly Code C1845 = Device Code X = P / F / E / U YWW = Date Code

#### **ORDERING INFORMATION**

Device	Package	Shipping
KSC1845FTA	TO-92 3L (Pb-Free)	2000 / Fan-Fold

#### KSC1845

### **ELECTRICAL CHARACTERISTICS** (Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

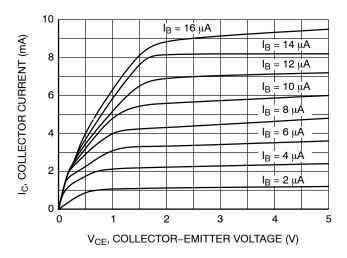
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_A = 0$	120	-	-	V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1 mA, I <sub>B</sub> = 0	120	-	_	V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	5	-	-	V
I <sub>CBO</sub>	Collector Cut-Off Current	V <sub>CB</sub> = 120 V, I <sub>E</sub> = 0	-	-	50	nA
I <sub>EBO</sub>	Emitter Cut-Off Current	V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0	-	-	50	nA
h <sub>FE1</sub>	DC Current Gain	V <sub>CE</sub> = 6 V, I <sub>C</sub> = 0.1 mA	150	580	-	
h <sub>FE2</sub>		V <sub>CE</sub> = 6 V, I <sub>C</sub> = 1 mA	200	600	1200	
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA}$	0.55	0.59	0.65	V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1 mA	=	0.07	0.30	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = 6 V, I <sub>C</sub> = 1 mA	50	100	-	MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 30 V, I <sub>E</sub> = 0, f = 1 MHz	-	1.6	2.5	pF
NF	Noise Figure	$V_{CE} = -5 \text{ V, } I_{C} = -1.0 \text{ mA,}$ $R_{S} = 100 \text{ k}\Omega, f = 1 \text{ kHz}$	-	7	-	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## $h_{\mbox{\scriptsize FE}}$ CLASSIFICATION

Classification	Р	F	E	U
h <sub>FE2</sub>	200~400	300~600	400~800	600~1200

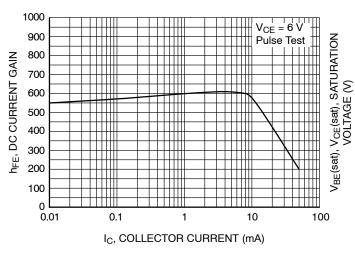
#### TYPICAL PERFORMANCE CHARACTERISTICS



1.0  $I_B = 1.4 \mu A$  $I_{B}^{\prime} = 1.2 \, \mu A$ IC, COLLECTOR CURRENT (mA)  $I_B = 1.0 \mu A$ 0.8  $I_B = 0.8 \, \mu A$ 0.6  $I_B = 0.6 \, \mu A$  $I_B = 0.4 \, \mu A$ 0.4  $I_B = 0.2 \,\mu A$ 0.2 0 0 20 40 60 80 100 V<sub>CE</sub>, COLLECTOR-EMITTER VOLTAGE (V)

Figure 1. Static Characteristic

Figure 2. Static Characteristic



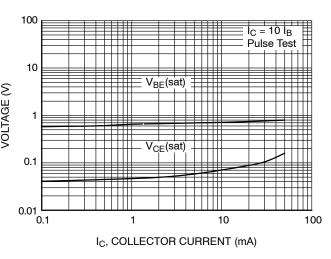
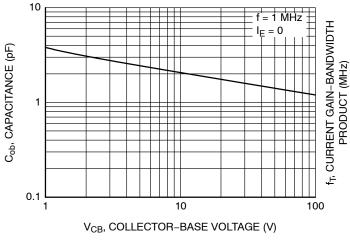


Figure 3. DC Current Gain

Figure 4. Base–Emitter Saturation Voltage and Collector–Emitter Saturation Voltage



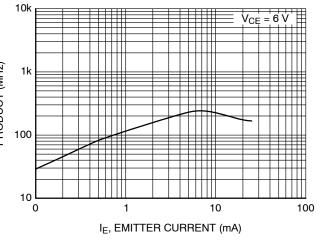
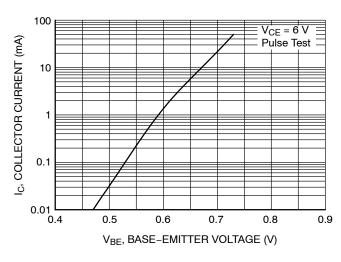


Figure 5. Collector Output Capacitance

Figure 6. Current Gain Bandwidth Product

#### KSC1845

### TYPICAL PERFORMANCE CHARACTERISTICS (Continued)



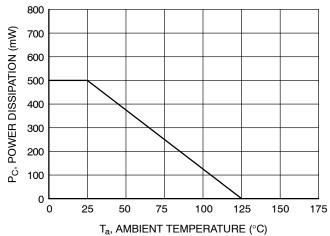


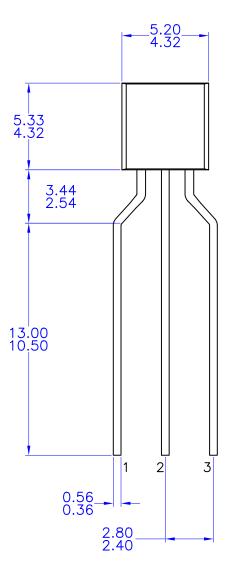
Figure 7. Collector Current vs. Base-Emitter Voltage

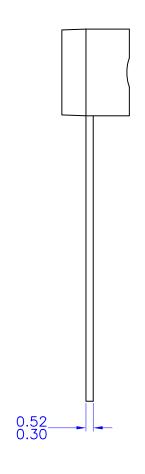
Figure 8. Power Derating

#### TO-92 3 4.83x4.76 LEADFORMED

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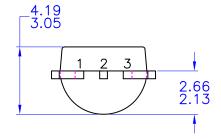
**DATE 30 SEP 2016** 





NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994



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